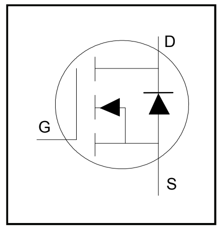
International
IOR Rectifier

StrongIRFET™
IRF200B211

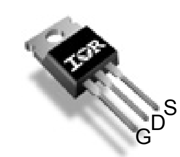
Application
- Brushed Motor drive applications
- BLDC Motor drive applications
- Battery powered circuits
- Half-bridge and full-bridge topologies
- Synchronous rectifier applications
- Resonant mode power supplies
- DC/DC and AC/DC converters
- DC/AC Inverters

HEXFET® Power MOSFET



V_{DSS}		200V
$R_{DS(on)}$	typ.	135mΩ
	max	170mΩ
I_D (Silicon Limited)		12A

Benefits
- Improved Gate, Avalanche and Dynamic dV/dt Ruggedness
- Fully Characterized Capacitance and Avalanche SOA
- Enhanced body diode dV/dt and dI/dt Capability
- Lead-Free*, RoHS Compliant, Halogen-Free



TO-220AB
IRF200B211

G	D	S
Gate	Drain	Source

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRF200B211	TO-220	Tube	50	IRF200B211

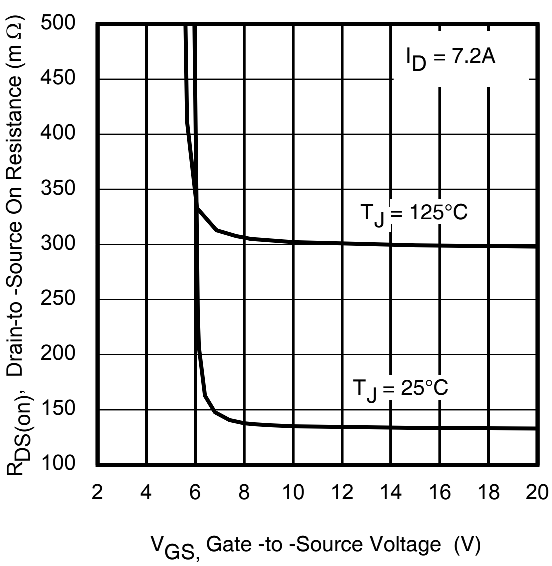


Fig 1. Typical On-Resistance vs. Gate Voltage

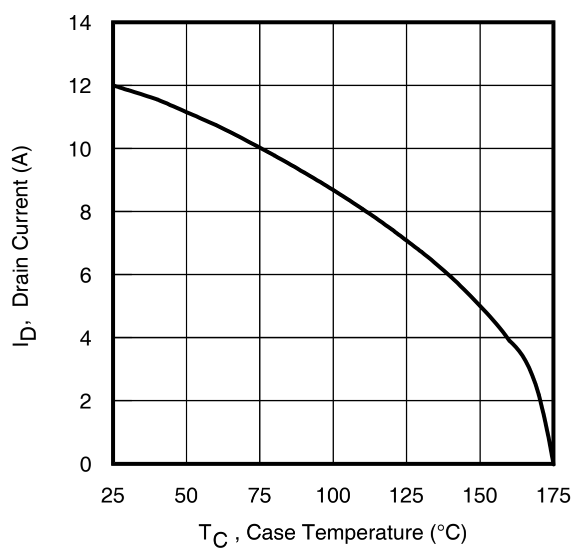


Fig 2. Maximum Drain Current vs. Case Temperature

Absolute Maximum Rating

Symbol	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, VGS @ 10V (Silicon Limited)	12	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V (Silicon Limited)	9.0	
I_{DM}	Pulsed Drain Current ②	34	
P_D @T_C = 25°C	Maximum Power Dissipation	80	W
	Linear Derating Factor	0.53	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	
	Mounting Torque, 6-32 or M3 Screw	10 lbf·in (1.1 N·m)	

Avalanche Characteristics

$E_{AS\ (Thermally\ limited)}$	Single Pulse Avalanche Energy ②	88	mJ
$E_{AS\ (Thermally\ limited)}$	Single Pulse Avalanche Energy ⑧	72	
$E_{AS\ (tested)}$	Single Pulse Avalanche Energy Tested Value ⑨	98	
I_{AR}	Avalanche Current ①	See Fig 15, 16, 23a, 23b	A
E_{AR}	Repetitive Avalanche Energy ①		mJ

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ⑦	——	1.88	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat Greased Surface	0.50	——	
$R_{\theta JA}$	Junction-to-Ambient	——	62	

Static @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	200	——	——	V	V_{GS} = 0V, I_D = 250μA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	——	0.21	——	V/°C	Reference to 25°C, I_D = 1mA ①
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	——	135	170	mΩ	V_{GS} = 10V, I_D = 7.2A ④
$V_{GS(th)}$	Gate Threshold Voltage	3.0	——	4.9	V	V_{DS} = V_{GS}, I_D = 50μA
I_{DSS}	Drain-to-Source Leakage Current	——	——	20	μA	V_{DS} = 200V, V_{GS} = 0V
		——	——	250		V_{DS} = 160V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Forward Leakage	——	——	100	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	——	——	-100		V_{GS} = -20V
R_G	Gate Resistance	——	2.7	——	Ω	

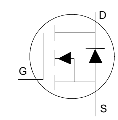
Notes:

① Repetitive rating; pulse width limited by max. junction temperature.
② Limited by T_{Jmax}, starting T_J = 25°C, L = 3.4mH, R_G = 50Ω, I_{AS} = 7.2A, V_{GS} =10V.
③ $I_{SD} \leq$ 7.2A, di/dt $\leq$ 1184A/μs, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq$ 175°C.
④ Pulse width $\leq$ 400μs; duty cycle $\leq$ 2%.
⑤ C_{oss} eff. (TR) is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.
⑥ C_{oss} eff. (ER) is a fixed capacitance that gives the same energy as C_{oss} while VDS is rising from 0 to 80% V_{DSS}.
⑦ R_θ is measured at T_J approximately 90°C.
⑧ Limited by T_{Jmax}, starting T_J = 25°C, L = 1.0mH, R_G = 50Ω, I_{AS} = 11.5A, V_{GS} =10V.
⑨ This value determined from sample failure population, starting T_J = 25°C, L= 3.4mH, R_G = 50Ω, I_{AS} = 7.2A, V_{GS} =10V.

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
gfs	Forward Transconductance	13	——	——	S	V_{DS} = 50V, I_D = 7.2A
Q_g	Total Gate Charge	——	15.3	23		I_D = 7.2A
Q_{gs}	Gate-to-Source Charge	——	5.1	——	nC	V_{DS} = 100V
Q_{gd}	Gate-to-Drain Charge	——	5.6	——		V_{GS} = 10V④
Q_{sync}	Total Gate Charge Sync. (Qg– Qgd)	——	10.2	——		
$t_{d(on)}$	Turn-On Delay Time	——	6.5	——		V_{DD} = 130V
t_r	Rise Time	——	9.5	——	ns	I_D = 7.2A
$t_{d(off)}$	Turn-Off Delay Time	——	11.3	——		R_G= 2.7Ω
t_f	Fall Time	——	6.5	——		V_{GS} = 10V④
C_{iss}	Input Capacitance	——	790	——		V_{GS} = 0V
C_{oss}	Output Capacitance	——	62	——		V_{DS} = 50V
C_{rss}	Reverse Transfer Capacitance	——	21	——	pF	f = 1.0MHz, See Fig.TBD
$C_{oss\ eff.(ER)}$	Effective Output Capacitance (Energy Related)	——	66	——		V_{GS} = 0V, VDS = 0V to 160V⑥
$C_{oss\ eff.(TR)}$	Output Capacitance (Time Related)	——	83	——		V_{GS} = 0V, VDS = 0V to 160V⑤

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	——	——	12	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	——	——	34		
V_{SD}	Diode Forward Voltage	——		1.3	V	T_J = 25°C, I_S = 7.2A,V_{GS} = 0V ④
dv/dt	Peak Diode Recovery dv/dt③	——	32.5	——	V/ns	T_J =175°C,I_S = 7.2A,V_{DS} = 200V
t_{rr}	Reverse Recovery Time	——	68	——	ns	T_J = 25°C V_{DD} = 100V
		——	83	——		T_J = 125°C I_F = 7.2A,
Q_{rr}	Reverse Recovery Charge	——	195	——	nC	T_J = 25°C di/dt = 100A/μs ④
		——	280	——		T_J = 125°C
I_{RRM}	Reverse Recovery Current	——	4.3	——	A	T_J = 25°C

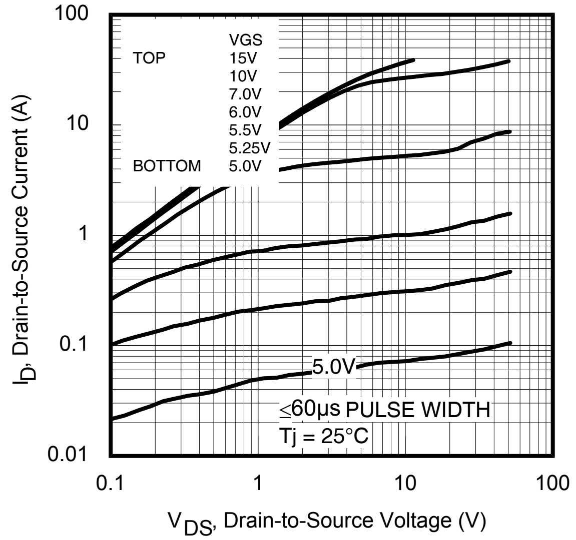


Fig 3. Typical Output Characteristics

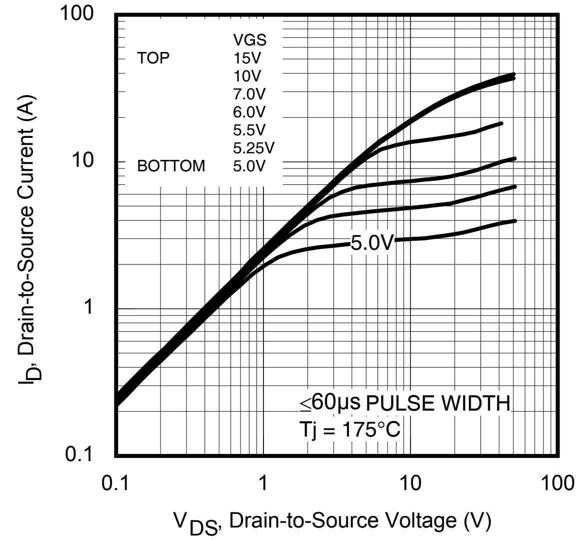


Fig 4. Typical Output Characteristics

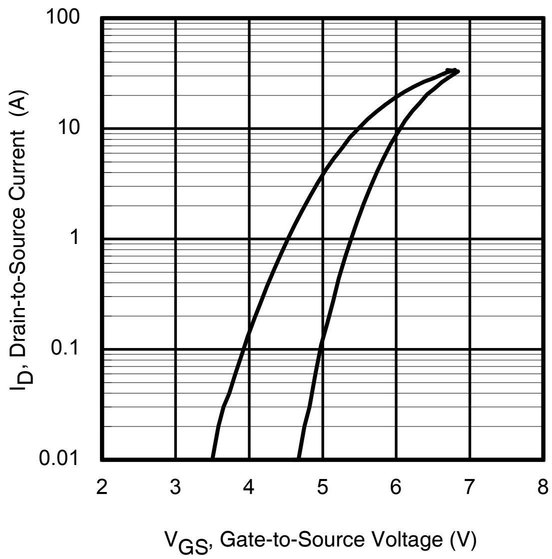


Fig 5. Typical Transfer Characteristics

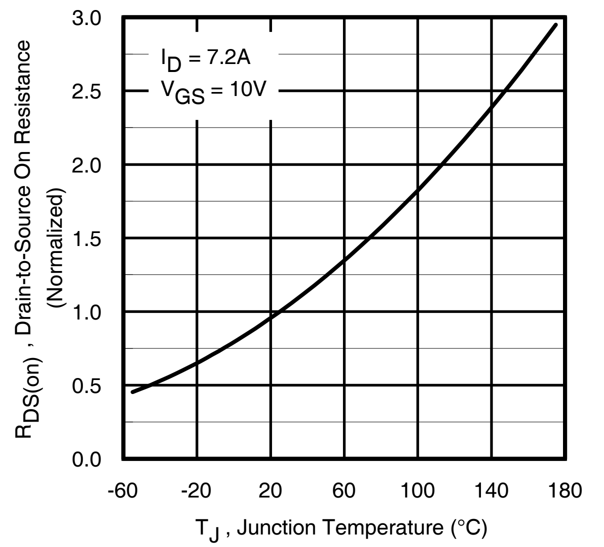


Fig 6. Normalized On-Resistance vs. Temperature

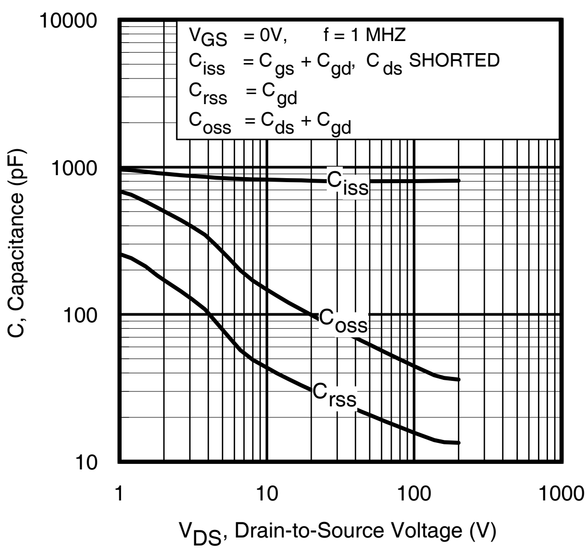


Fig 7. Typical Capacitance vs. Drain-to-Source Voltage

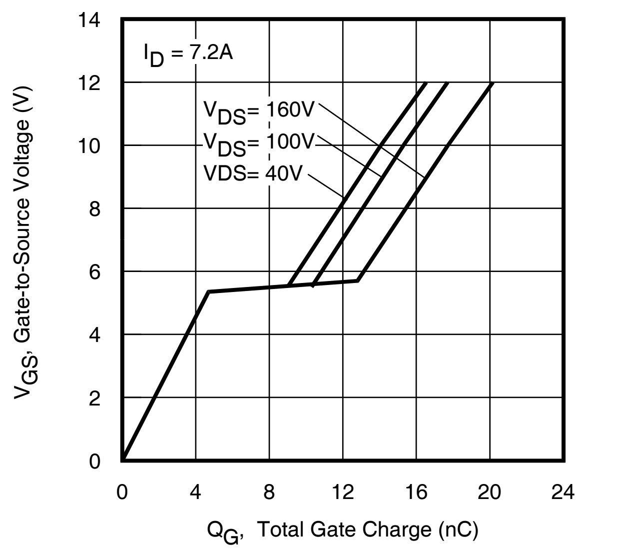


Fig 8. Typical Gate Charge vs.Gate-to-Source Voltage

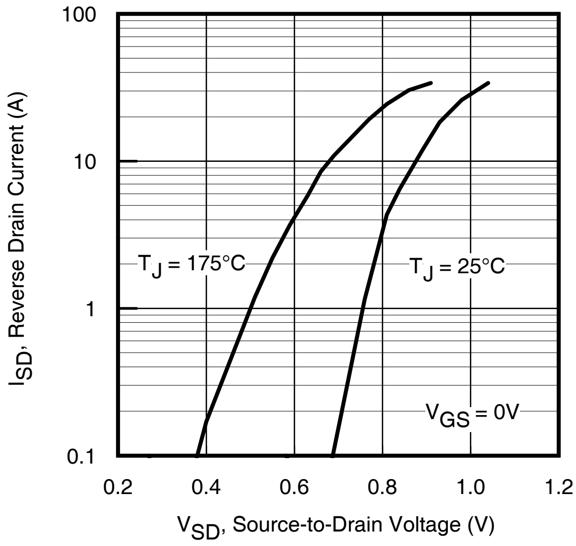


Fig 9. Typical Source-Drain Diode Forward Voltage

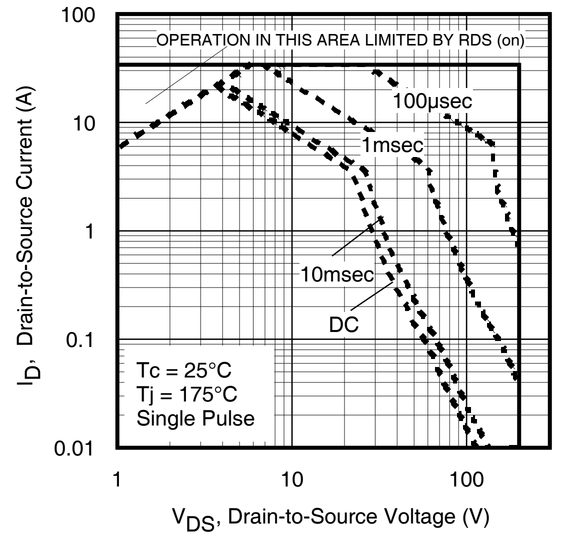


Fig 10. Maximum Safe Operating Area

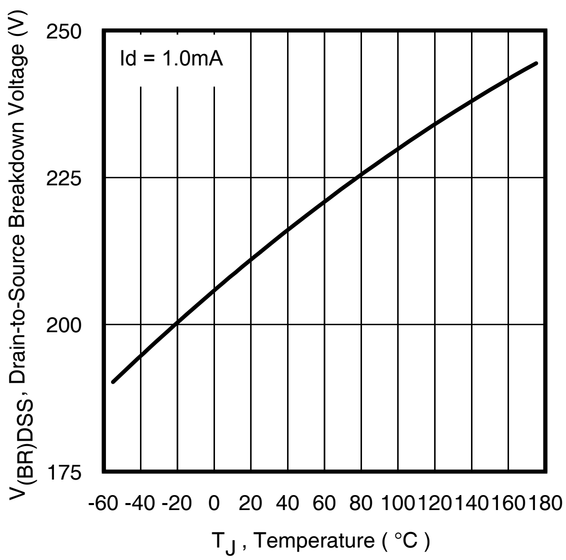


Fig 11. Drain-to-Source Breakdown Voltage

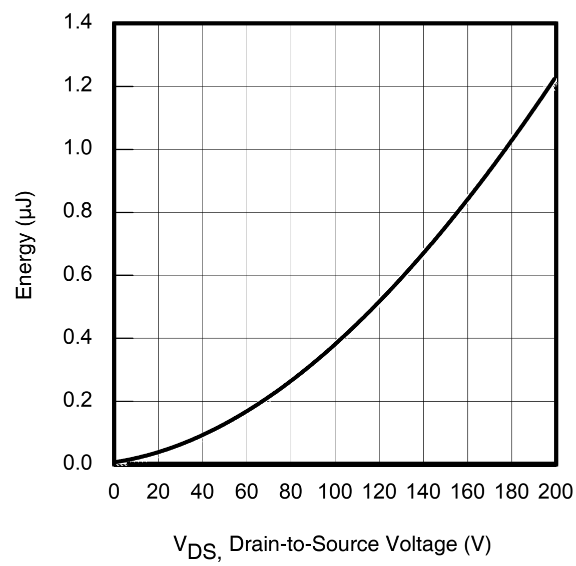


Fig 12. Typical C_{oss} Stored Energy

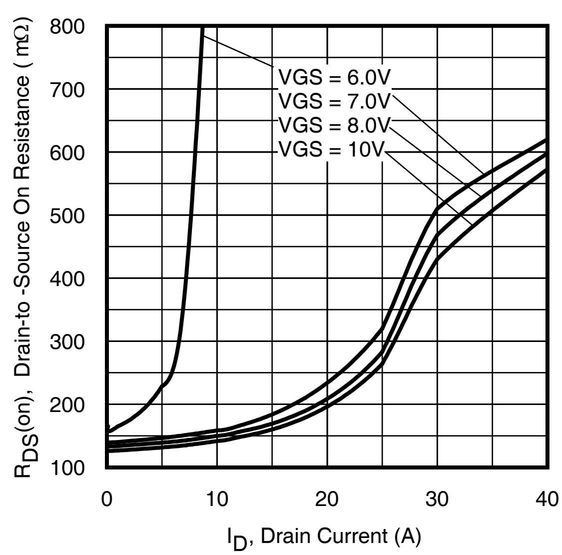


Fig 13. Typical On– Resistance vs. Drain Current

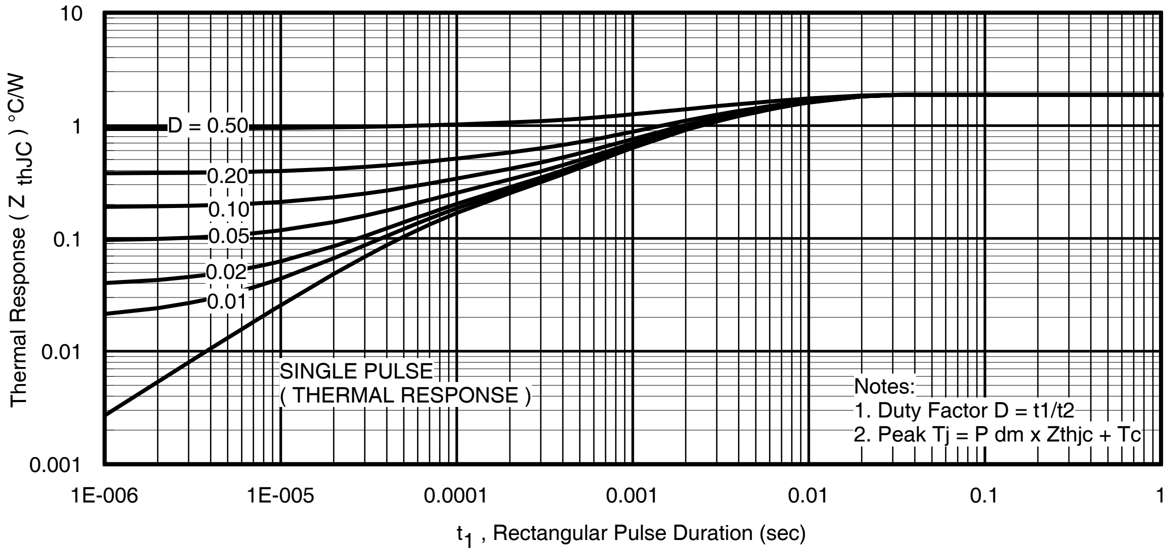


Fig 14. Maximum Effective Transient Thermal Impedance, Junction-to-Case

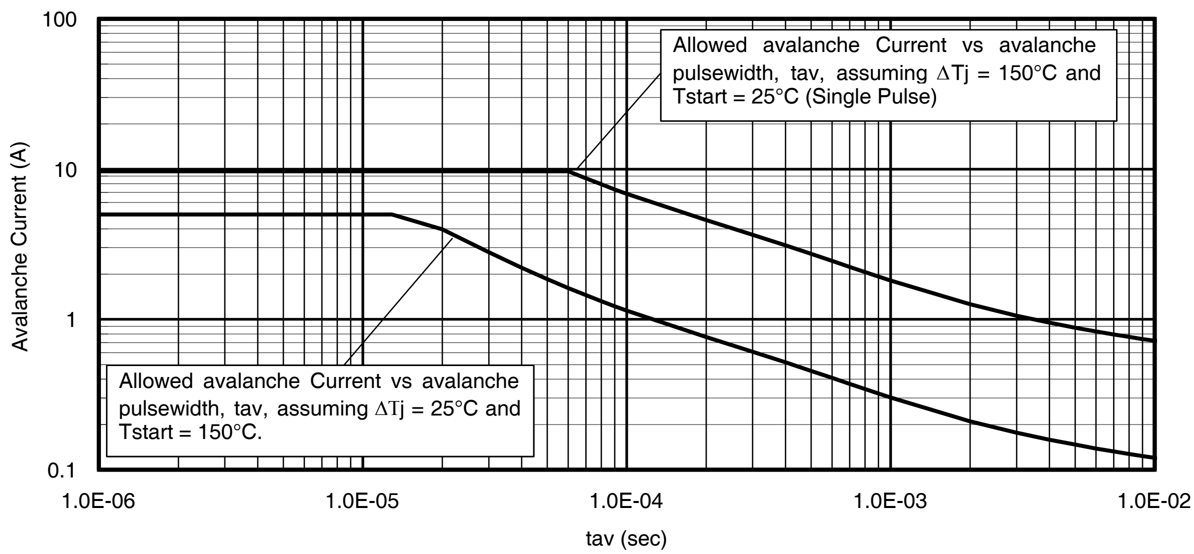


Fig 15. Avalanche Current vs. Pulse Width

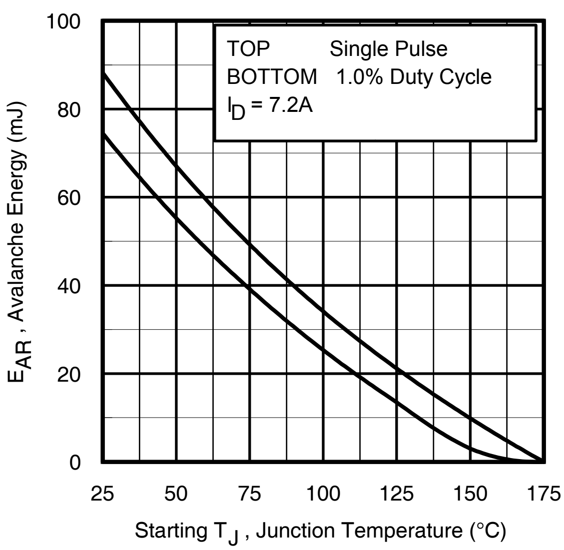


Fig 16. Maximum Avalanche Energy vs. Temperature

Notes on Repetitive Avalanche Curves , Figures 15, 16:
(For further info, see AN-1005 at www.irf.com)

1.Avalanche failures assumption:
Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax}. This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 23a, 23b.
4. $P_{D\ (ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 14, 15).

t_{av} = Average time in avalanche.
D = Duty cycle in avalanche = $t_{av} \cdot f$
$Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see Figures 14)

$$PD\ (ave) = 1/2\ (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$
$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$
$$E_{AS\ (AR)} = P_{D\ (ave)} \cdot t_{av}$$

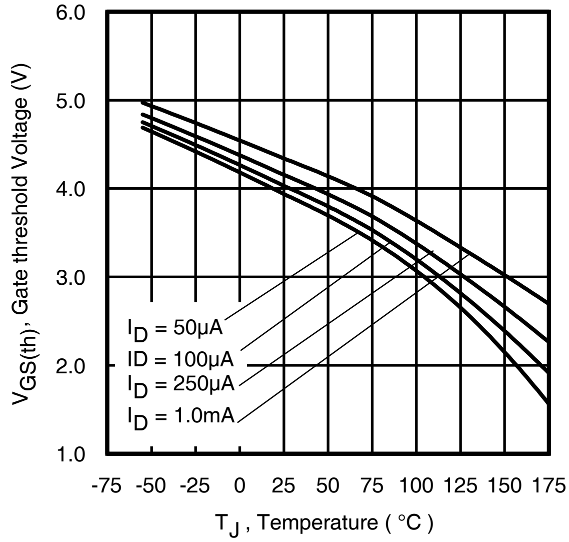


Fig 17. Threshold Voltage vs. Temperature

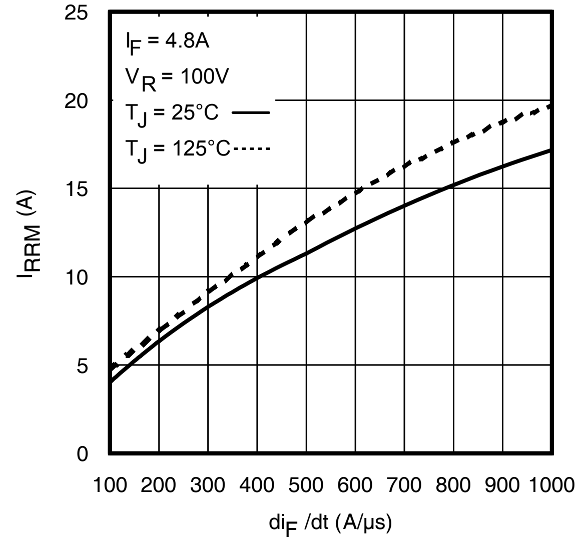


Fig 18. Typical Recovery Current vs. dif/dt

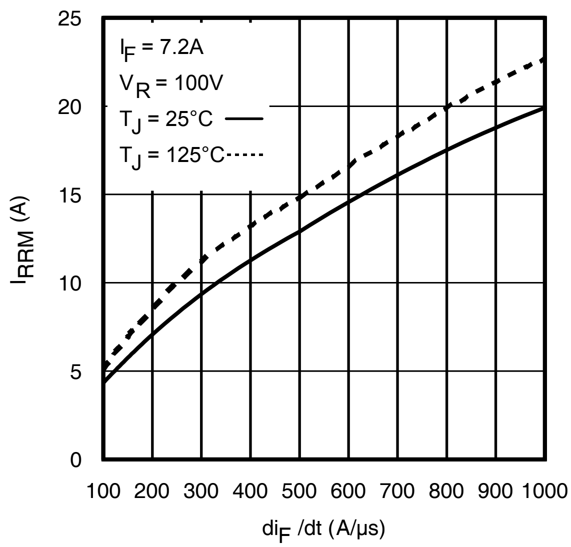


Fig 19. Typical Recovery Current vs. dif/dt

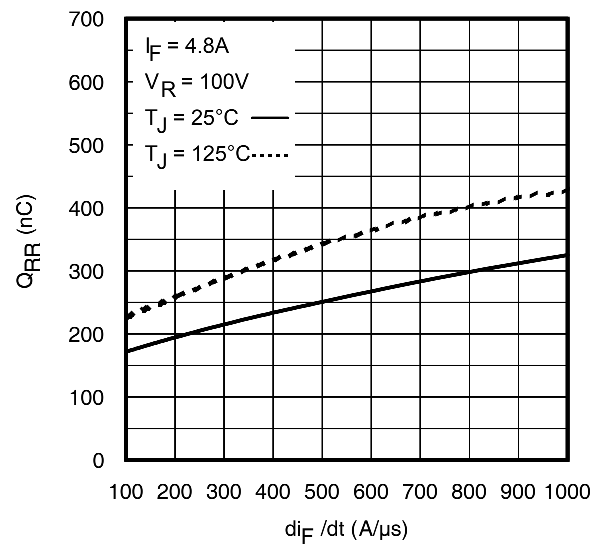


Fig 20. Typical Stored Charge vs. dif/dt

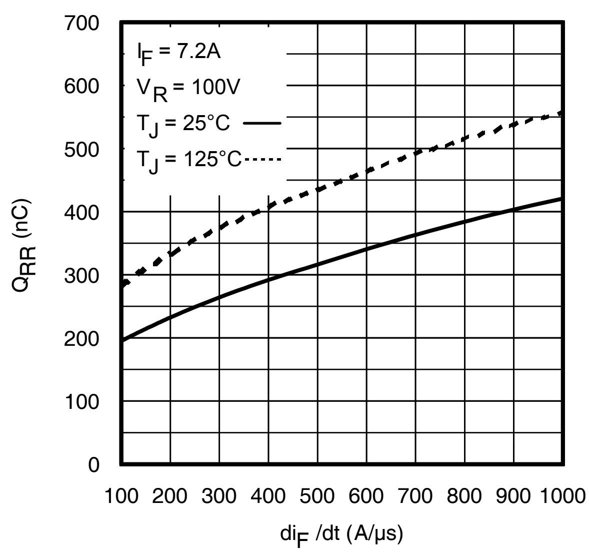


Fig 21. Typical Stored Charge vs. dif/dt

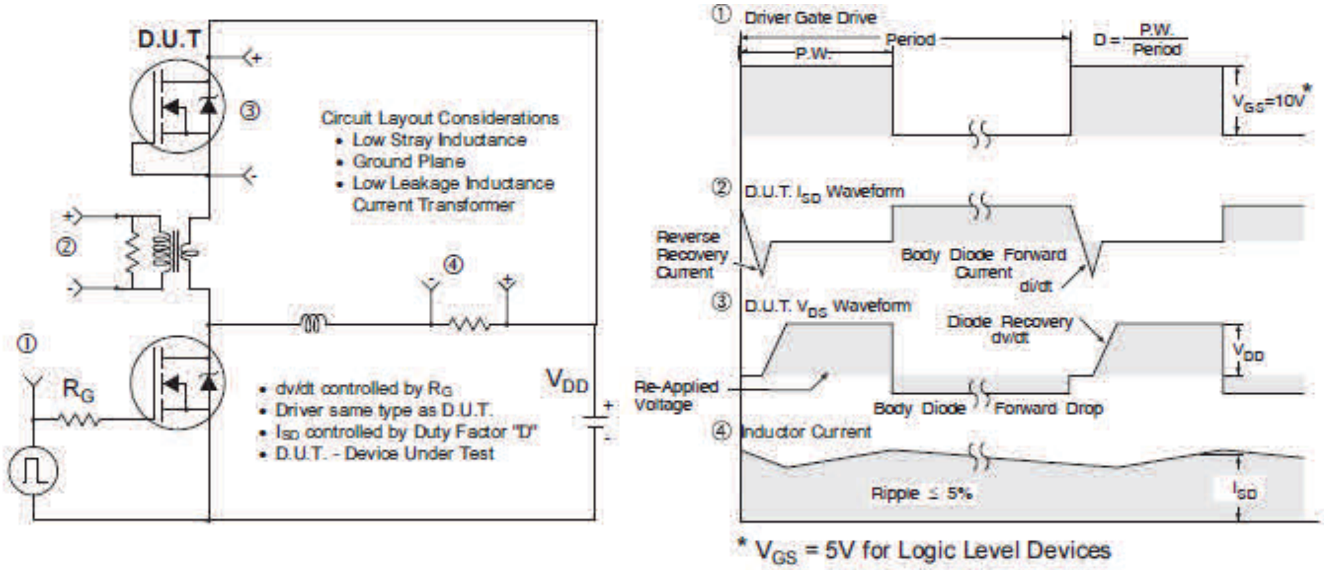


Fig 22. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

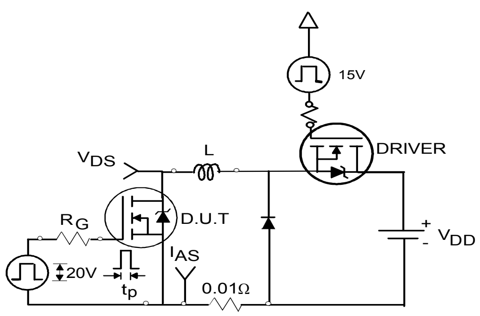


Fig 23a. Unclamped Inductive Test Circuit

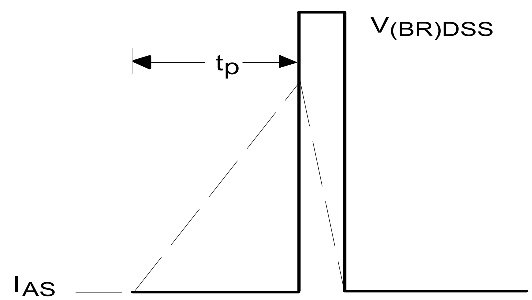


Fig 23b. Unclamped Inductive Waveforms

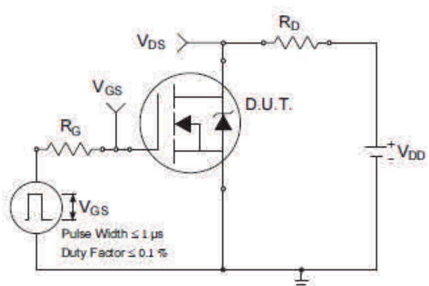


Fig 24a. Switching Time Test Circuit

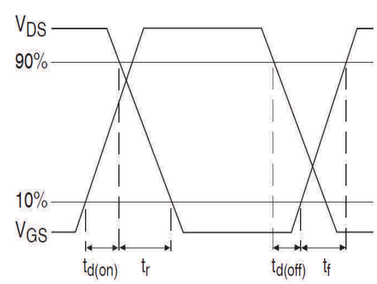


Fig 24b. Switching Time Waveforms

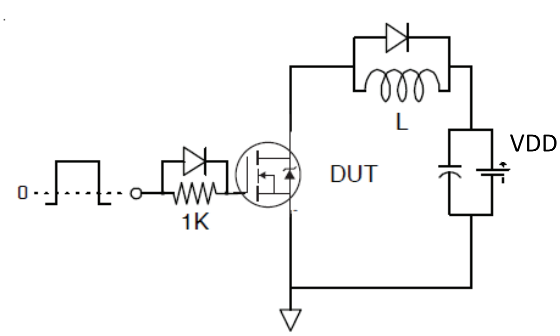


Fig 25a. Gate Charge Test Circuit

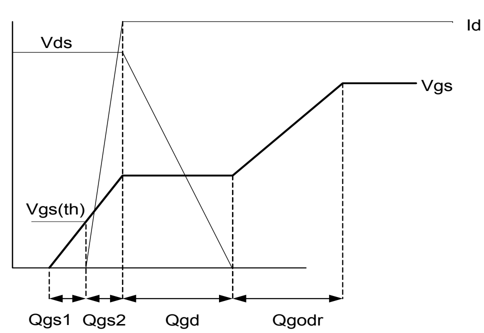
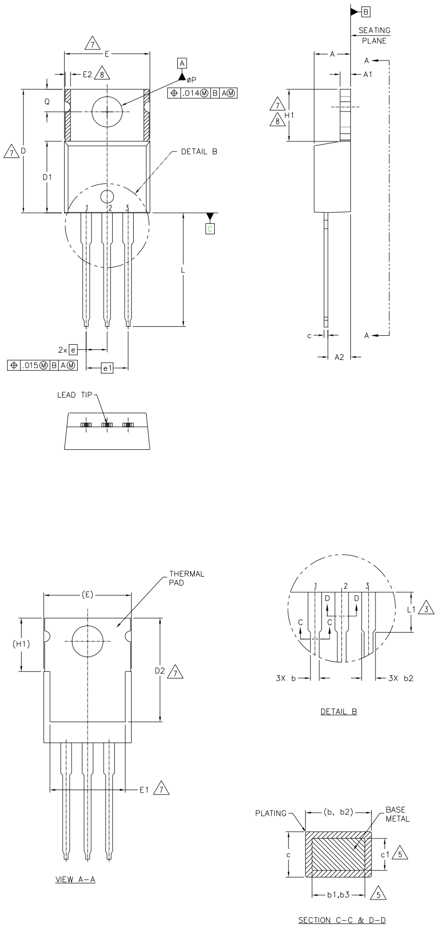


Fig 25b. Gate Charge Waveform

TO-220AB Package Outline (Dimensions are shown in millimeters (inches))



NOTES:

1.– DIMENSIONING AND TOLERANCING AS PER ASME Y14.5 M– 1994.
2.– DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
3.– LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
4.– DIMENSION D, D1 & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5.– DIMENSION b1, b3 & c1 APPLY TO BASE METAL ONLY.
6.– CONTROLLING DIMENSION : INCHES.
7.– THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E,H1,D2 & E1
8.– DIMENSION E2 X H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRREGULARITIES ARE ALLOWED.
9.– OUTLINE CONFORMS TO JEDEC TO-220, EXCEPT A2 (max.) AND D2 (min.) WHERE DIMENSIONS ARE DERIVED FROM THE ACTUAL PACKAGE OUTLINE.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	3.56	4.83	.140	.190	
A1	1.14	1.40	.045	.055	
A2	2.03	2.92	.080	.115	
b	0.38	1.01	.015	.040	
b1	0.38	0.97	.015	.038	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.36	0.61	.014	.024	
c1	0.36	0.56	.014	.022	5
D	14.22	16.51	.560	.650	4
D1	8.38	9.02	.330	.355	
D2	11.68	12.88	.460	.507	7
E	9.65	10.67	.380	.420	4,7
E1	6.86	8.89	.270	.350	7
E2	–	0.76	–	.030	8
e	2.54 BSC		.100 BSC		
e1	5.08 BSC		.200 BSC		
H1	5.84	6.86	.230	.270	7,8
L	12.70	14.73	.500	.580	
L1	3.56	4.06	.140	.160	3
ØP	3.54	4.08	.139	.161	
Q	2.54	3.42	.100	.135	

LEAD ASSIGNMENTS

HEXFET

1.– GATE
2.– DRAIN
3.– SOURCE

IGBTs, CoPACK

1.– GATE
2.– COLLECTOR
3.– EMITTER

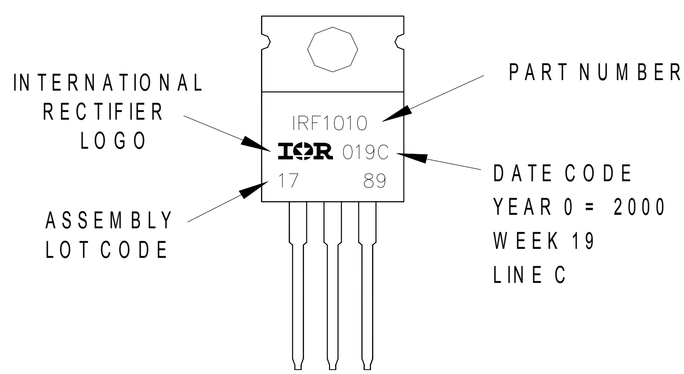
DIODES

1.– ANODE
2.– CATHODE
3.– ANODE

TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010
LOT CODE 1789
ASSEMBLED ON WW 19, 2000
IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position indicates "Lead - Free"



TO-220AB packages are not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

Qualification Information†

Qualification Level	Industrial (per JEDEC JESD47F) ††	
Moisture Sensitivity Level	TO-220	N/A
RoHS Compliant	Yes	

† Qualification standards can be found at International Rectifier's web site: http://www.irf.com/product-info/reliability/

†† Applicable version of JEDEC standard at the time of product release.

International Rectifier

IR WORLD HEADQUARTERS: 101 N. Sepulveda Blvd., El Segundo, California 90245, USA
To contact International Rectifier, please visit http://www.irf.com/whoto-call/

